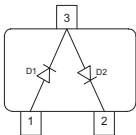
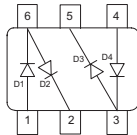


Silicon Switching Diode

- For high-speed switching applications
- Connected in series


BAV99/T/W

BAV99S/U


Type	Package	Configuration	Marking
BAV99	SOT23	series	A7s
BAV99S	SOT363	dual series	A7s
BAV99T	SC75	series	A7s
BAV99U	SC74	dual series	A7s
BAV99W	SOT323	series	A7s

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Peak reverse voltage	V_{RM}	85	
Forward current	I_F	200	mA
Surge forward current, $t = 1 \mu\text{s}$	I_{FS}	4.5	A
Total power dissipation	P_{tot}		mW
BAV99, $T_S \leq 31^\circ\text{C}$		330	
BAV99S, $T_S \leq 85^\circ\text{C}$		250	
BAV99T, $T_S \leq 104^\circ\text{C}$		250	
BAV99U, $T_S \leq 113^\circ\text{C}$		250	
BAV99W, $T_S \leq 110^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BAV99		≤ 360	
BAV99S		≤ 260	
BAV99T		≤ 185	
BAV99U		≤ 150	
BAV99W		≤ 160	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

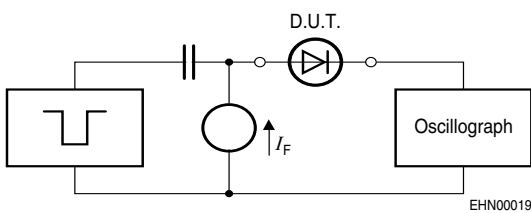
DC Characteristics

Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	85	-	-	V
Reverse current $V_R = 70 \text{ V}$ $V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$ $V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$	I_R	-	-	0.15 30 50	μA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 150 \text{ mA}$	V_F	-	-	715 855 1000 1200 1250	mV

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_T	-	-	1.5	pF
Reverse recovery time $I_F = 10\text{ mA}, I_R = 10\text{ mA}$, measured at $I_R = 1\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	-	-	4	ns

Test circuit for reverse recovery time

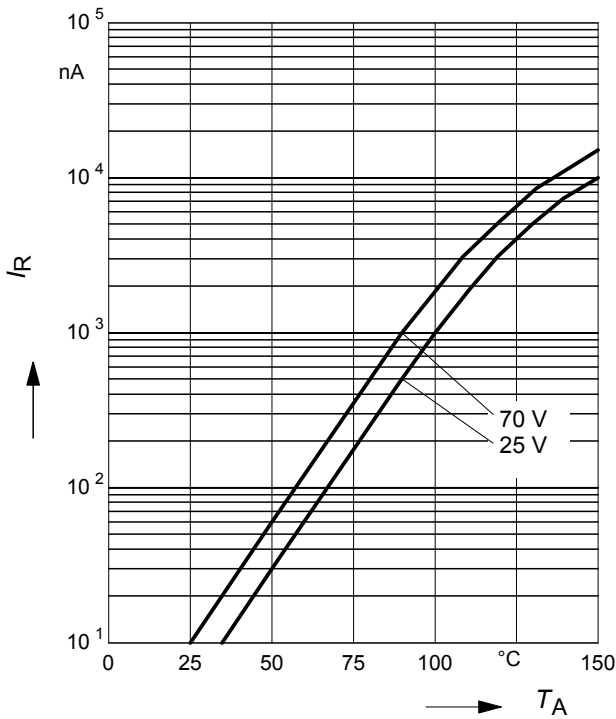


Pulse generator: $t_p = 100\text{ ns}$, $D = 0.05$,
 $t_r = 0.6\text{ ns}$, $R_i = 50\ \Omega$

Oscilloscope: $R = 50$, $t_r = 0.35\text{ ns}$
 $C \leq 1\text{ pF}$

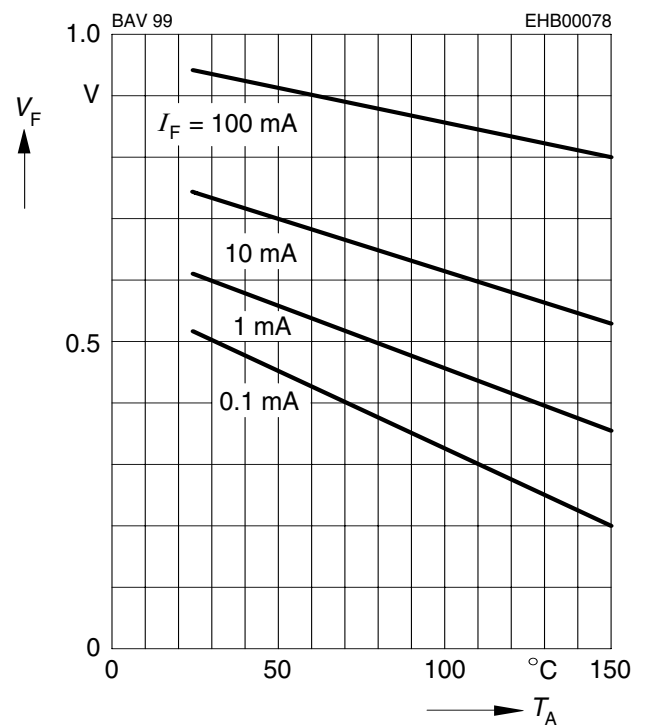
Reverse current $I_R = f(T_A)$

$V_R =$ Parameter



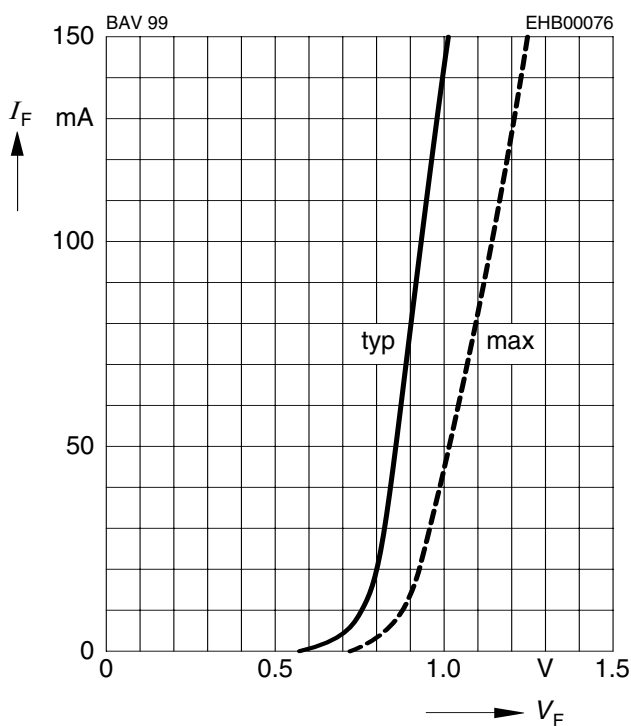
Forward Voltage $V_F = f(T_A)$

$I_F =$ Parameter



Forward current $I_F = f(V_F)$

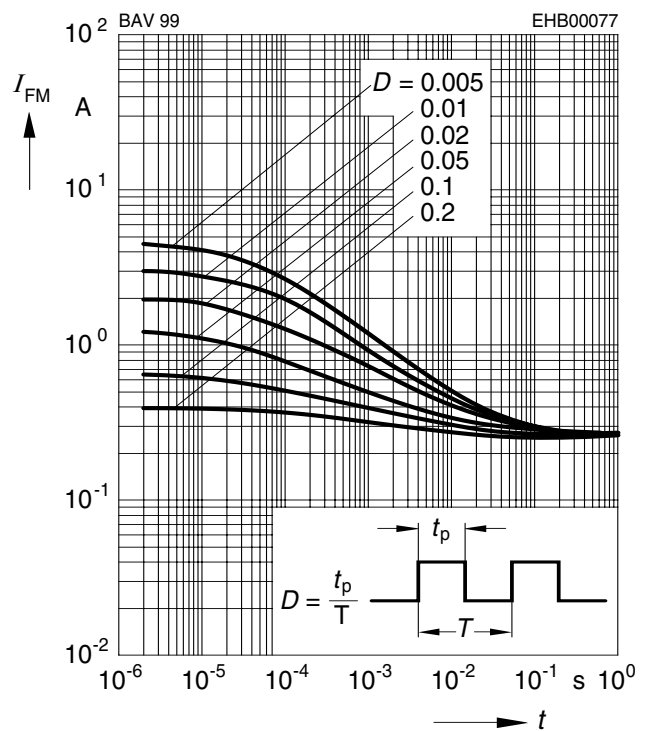
$T_A = 25^\circ\text{C}$



Peak forward current $I_{FM} = f(t_p)$

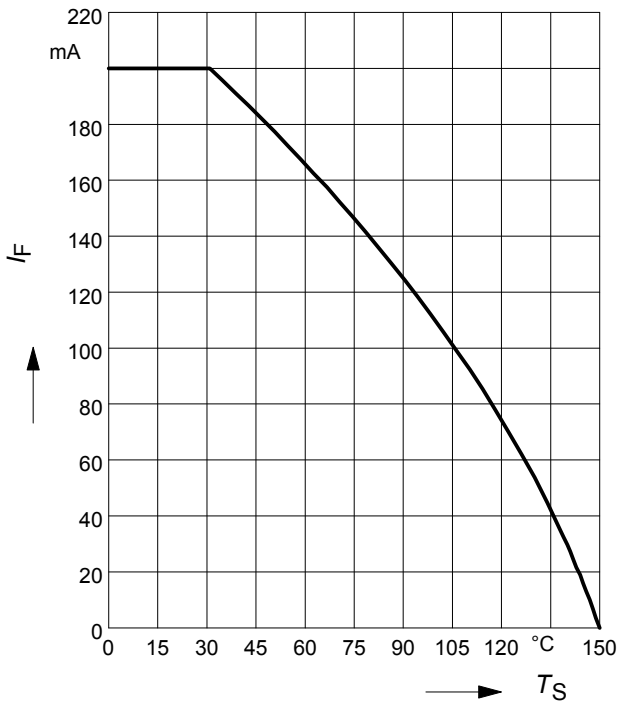
$T_A = 25^\circ\text{C}$

BAV99



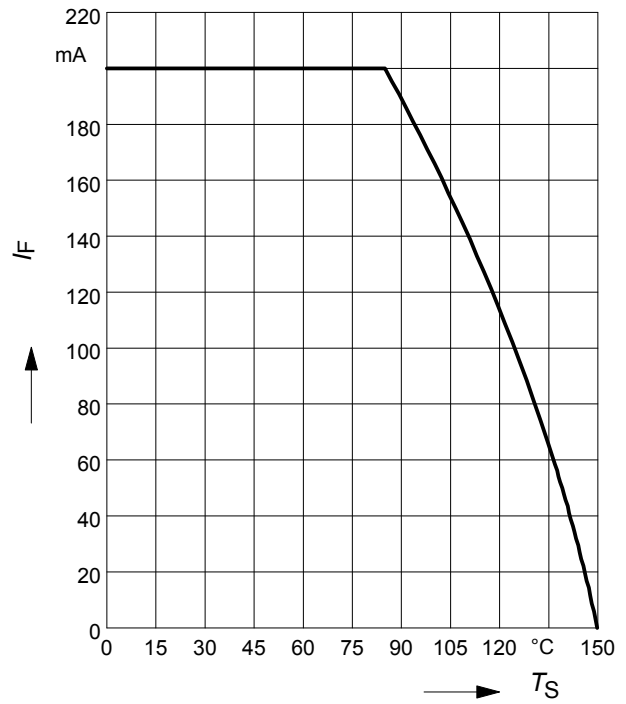
Forward current $I_F = f(T_S)$

BAV99



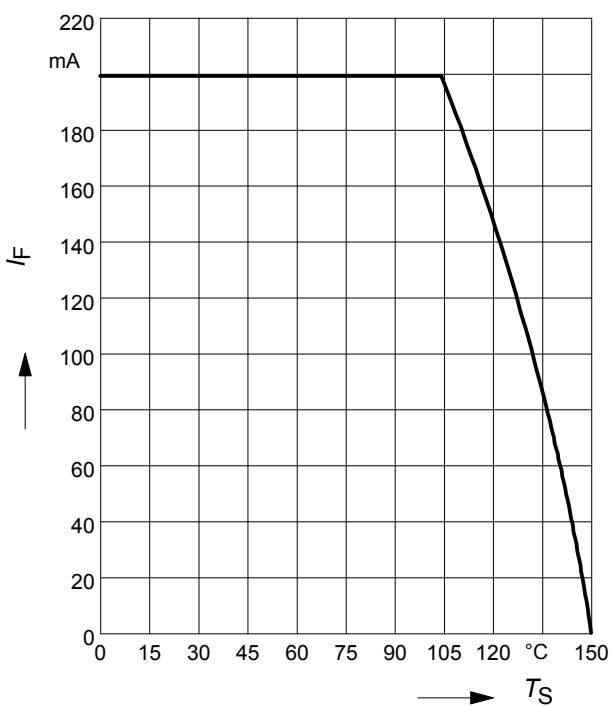
Forward current $I_F = f(T_S)$

BAV99S



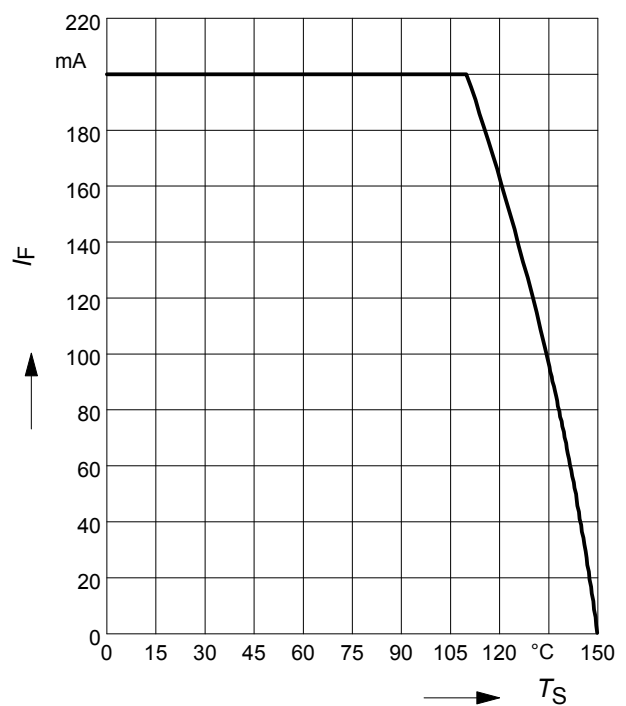
Forward current $I_F = f(T_S)$

BAV99T



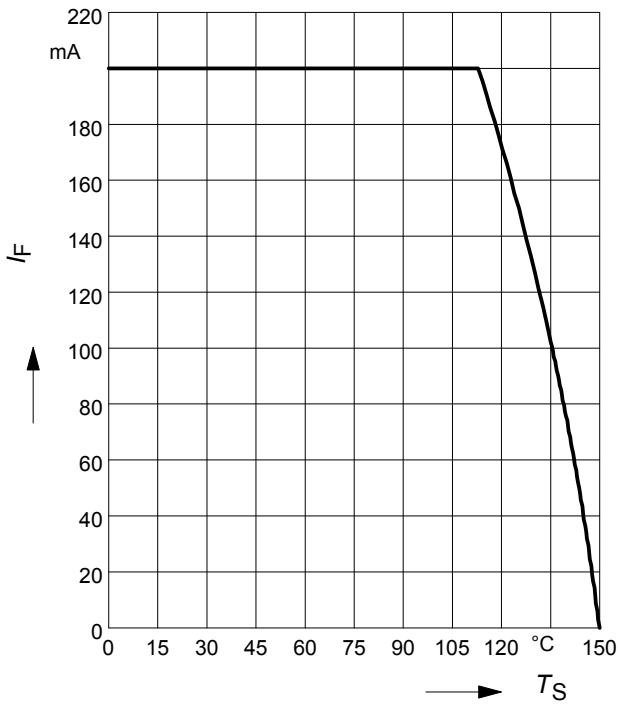
Forward current $I_F = f(T_S)$

BAV99U



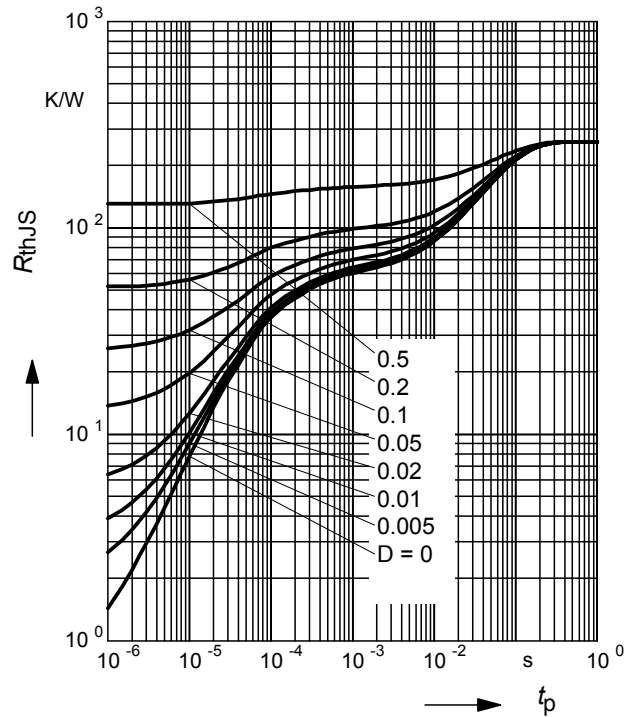
Forward current $I_F = f(T_S)$

BAV99W



Permissible Puls Load $R_{thJS} = f(t_p)$

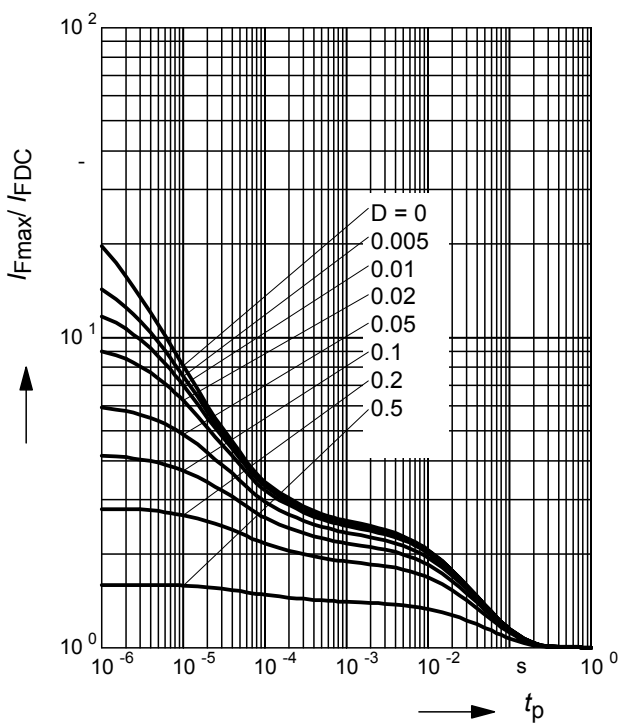
BAV99S



Permissible Pulse Load

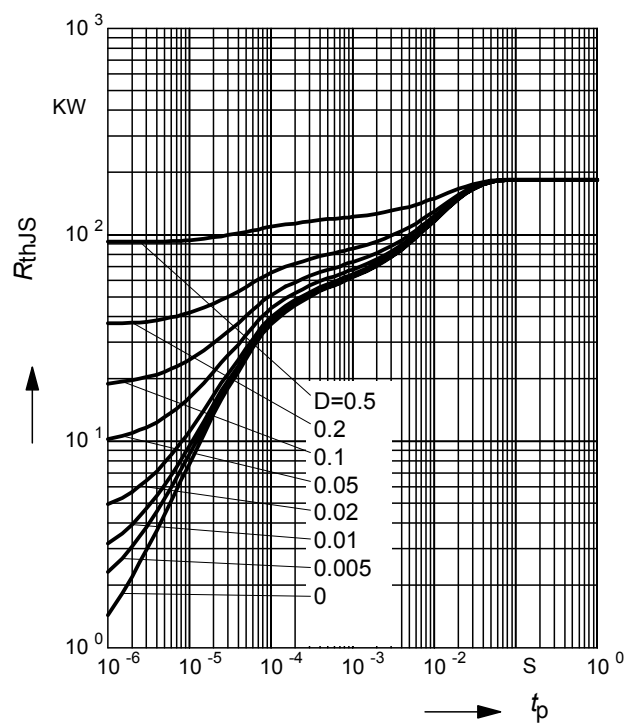
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV99S



Permissible Puls Load $R_{thJS} = f(t_p)$

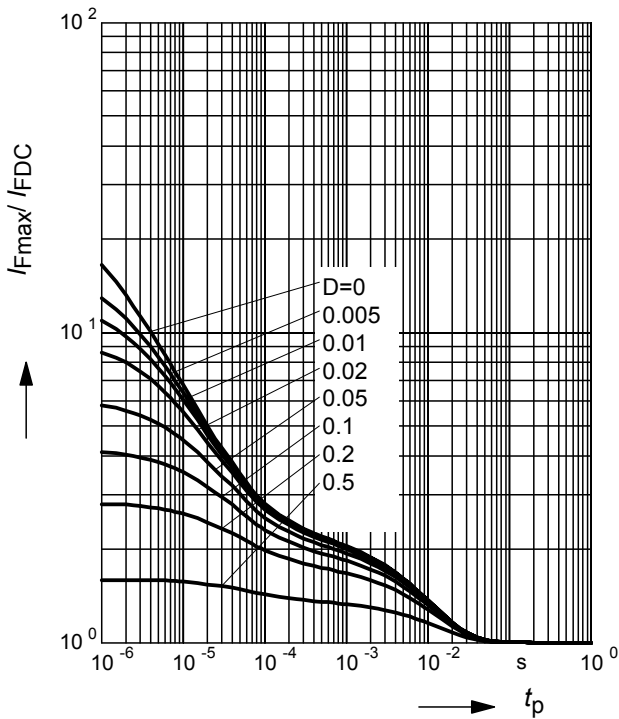
BAV99T



Permissible Pulse Load

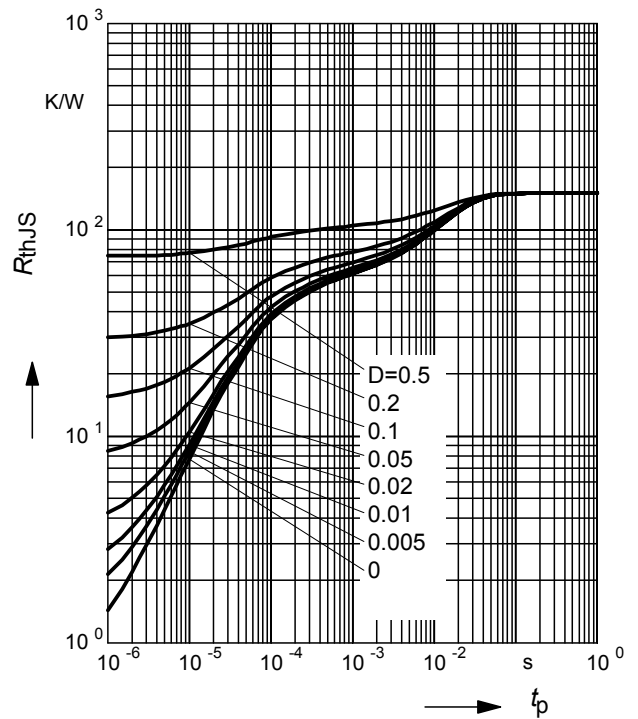
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV99T



Permissible Puls Load $R_{thJS} = f(t_p)$

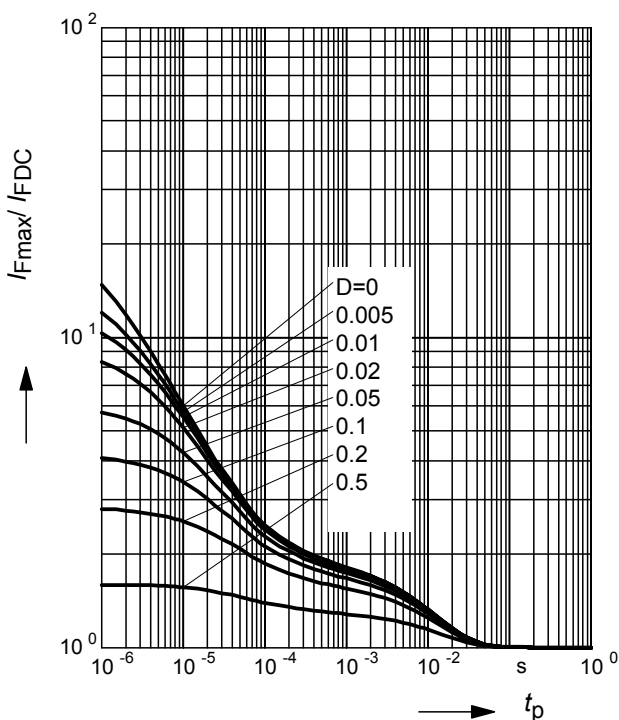
BAV99U



Permissible Pulse Load

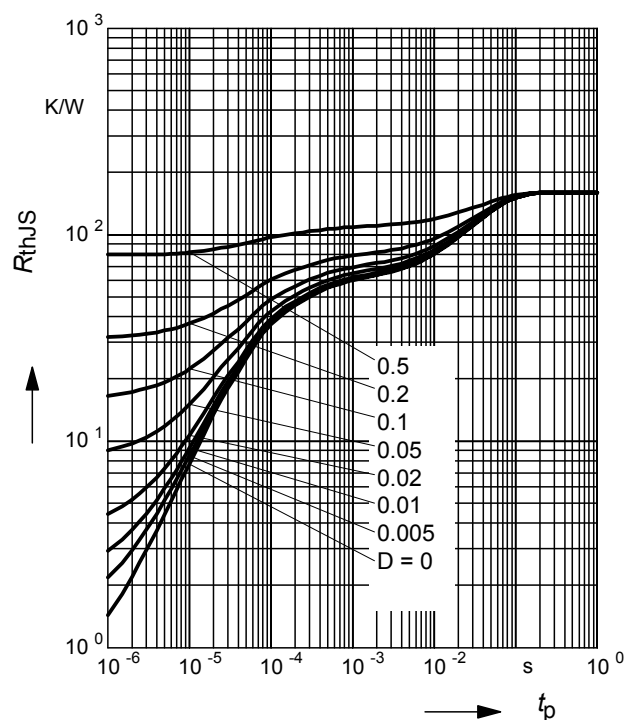
$I_{Fmax} / I_{FDC} = f(t_p)$

BAV99U



Permissible Puls Load $R_{thJS} = f(t_p)$

BAV99W



Permissible Pulse Load

$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAV99W

